Process Technology

C5: 0.5 μm **Process Technology**



ON Semiconductor®

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Overview

Optimized for 5 V mixed-signal applications, the C5 process family from ON Semiconductor offers a medium-density, high-performance mixed-signal technology capable of integrating complex analog functions, digital content and 20 V capability. This process delivers the advantages of a dedicated mixed-signal 0.5 µm process without the costs associated with the extra mask steps of a BCD process. Low-voltage transistors are also available for the 0.5 µm process making it well-suited for low-power applications.

Features

- 2 or 3 Metal Layers
- Poly to Poly Capacitors
- EEPROM
- Schottky Diodes
- High-voltage I/O 12/20 V
- High-resistance Poly
- Low-voltage Modules

PROCESS CHARACTERISTICS

Operating Voltage	5, 12 V	
Substrate Material	P-Type, Bulk or EPI	
Drawn Transistor Length	0.6 μm	
Gate Oxide Thickness	13.5 nm	
Contact/Via Size	0.5 μm	
Contacted Gate Pitch	3.9 μm	
Top Metal Thickness	675 nm	
Contacted Metal Pitch		
Metal 1	1.5 μm	
Metal 2, 3	1.6 μm	
Metal Composition	TiN/AlCu/TiN	

SAMPLE PROCESS OPTIONS

	Mask Layers*
Standard CMOS with 20 V extended drain	13/15
Plus double poly cap	14/16
All of the above plus 1,000 Ω /square resistor	15/17
All of the above plus 12 V gate	16/18
All of the above plus low V _t devices	19/21

^{*2} Metal / 3 Metal.

DEVICE CHARACTERISTICS

(All Values Typical at 25°C)

HIGH-VOLTAGE TRANSISTORS 12 V DUAL GATE NESTED DRAIN

N-Ch 12 V (NU)	Typical Value	Units
V _t	0.95	V
l _{dsat}	450	μ A /μm
B _{VDSS}	19	V
P-Ch 12 V (PU)	Typical Value	Units
V _t	-1.6	V
l _{dsat}	-110	μ A /μm
B _{VDSS}	-14.5	V

20 V EXTENDED DRAIN, 15 V GATE

1

N-Ch 20 V (NX)	Typical Value	Units
V _t	0.95	V
I _{dsat}	400	μ A /μm
B _{VDSS}	28	V
P-Ch 20 V (PU)	Typical Value	Units
V_{t}	-1.65	V
I _{dsat}	-130	μ A /μm
B _{VDSS}	-28	V

20 V EXTENDED DRAIN, 5 V GATE

N-Ch 20 V (NT)	Typical Value	Units
V _t	0.75	V
I _{dsat}	145	μ A /μm
B _{VDSS}	28	V
P-Ch 20 V (PT)	Typical Value	Units
V _t	-1.0	V
I _{dsat}	-55	μ A /μm
B _{VDSS}	-28	V

STANDARD TRANSISTORS

N-Channel	Typical Value	Units
V_{t}	0.7	V
I _{dsat}	450	μ A /μm
P-Channel	Typical Value	Units
V _t	-0.9	V

RESISTORS

	Typical Value	Units
Poly	25	Ω /square
Hi-R Poly	1000	Ω/square
N-Diffusion	80	Ω/square
P-Diffusion	110	Ω/square
N-Well	855	Ω/square

CAPACITORS

Poly-Poly	Typical Value	Units
Area	0.9	fF/μm²
Periphery	0.065	fF/μm

LIBRARIES

(All Values Typical at 3.3 V, 25°C)

Synthesis Libraries	(All values Typical at 0.0 v, 20 0)		
Simulation Libraries	Fr	ont–End Digital Design	
Analog – General Design Information (GDI) Spice Models	Digital	Synthesis Libraries	
Spice Models		Simulation Libraries	
Digital Design		Design Rules	
High Performance Core 4.2 K gates/mm² * 1.58 μW/MHz/gate 103 ps gate delay (2 Input NAND, fanout = 2) Tall Pads for High I/O Count Designs 86 μm in–line pad pitch 60 μm staggered pad pitch 558 μm pad height Mixed–Signal Design Cadence Technology File Cadence Transistor Library Mixed–Signal Core 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed–Signal Medium Height 4.2 K gates/mm² * 86 μm in–line pad pitch 128 ps gate delay (2 Input NAND, fanout = 2) 135 μm in–line pad pitch		Spice Models	
Tall Pads for High I/O Count Designs Cadence Technology File Cadence Transistor Library Mixed–Signal Core Mixed–Signal Design Design Design Design Design Design Design Design Separate substrate bus for reduced digital noise Technology File Cadence Transistor Library Mixed–Signal Core Technology File Cadence Transistor Library Mixed–Signal Design D		Digital Design	
1.58 μW/MHz/gate 103 ps gate delay (2 Input NAND, fanout = 2) Tall Pads for High I/O Count Designs 86 μm in-line pad pitch 60 μm staggered pad pitch 558 μm pad height Mixed-Signal Design Cadence Technology File Cadence Transistor Library Mixed-Signal Core 7.4 K gates/mm² * 0.63 μW/MHz/gate 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height 86 μm in-line pad pitch		4.2 K gates/mm ² *	
Tall Pads for High I/O Count Designs 86 μm in-line pad pitch 60 μm staggered pad pitch 558 μm pad height Mixed-Signal Design Separate substrate bus for reduced digital noise 7.4 K gates/mm² * Mixed-Signal Core 7.8 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height 86 μm in-line pad pitch	Core	1.58 μW/MHz/gate	
I/O Count Designs 60 μm staggered pad pitch 558 μm pad height Mixed-Signal Design Cadence Technology File Cadence Transistor Library Mixed-Signal Core 7.4 K gates/mm² * 0.63 μW/MHz/gate 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height 86 μm in-line pad pitch			
Cadence Technology File Cadence Transistor Library Mixed–Signal Design		86 μm in-line pad pitch	
Mixed-Signal Design Cadence Technology File Cadence Transistor Library Mixed-Signal Core Mixed-Signal Core Mixed-Signal Core Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height Mixed-Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height	I/O Count Designs	60 μm staggered pad pitch	
Cadence Technology File Cadence Transistor Library 7.4 K gates/mm² * Mixed-Signal Core 0.63 μW/MHz/gate 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs 135 μm in-line pad pitch Mixed-Signal Medium Height 86 μm in-line pad pitch		558 μm pad height	
Technology File Cadence Transistor Library Mixed–Signal Core Mixed Signal Short Pads for High Logic Contact Designs Mixed–Signal Mixed–Signal Mixed–Signal Mixed–Signal Mixed–Signal Medium Height noise 7.4 K gates/mm² * 0.63 μW/MHz/gate 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) 135 μm in–line pad pitch 388 μm pad height 86 μm in–line pad pitch		Mixed-Signal Design	
Transistor Library Mixed-Signal Core 0.63 μW/MHz/gate 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height 7.4 K gates/mm² * 7.4 K gates/mm² * 128 ps gate delay (2 Input NAND, fanout = 2) 389 μm in-line pad pitch 86 μm in-line pad pitch	Technology File		
Core 558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed–Signal Medium Height 558 μm pad height 135 μm in–line pad pitch 388 μm pad height		7.4 K gates/mm ² *	
558 μm pad height 128 ps gate delay (2 Input NAND, fanout = 2)		0.63 μW/MHz/gate	
(2 Input NAND, fanout = 2) Mixed Signal Short Pads for High Logic Contact Designs Mixed-Signal Medium Height (2 Input NAND, fanout = 2) 135 μm in–line pad pitch 86 μm in–line pad pitch	Core	558 μm pad height	
Short Pads for High Logic Contact Designs Mixed-Signal Medium Height 86 µm in-line pad pitch			
Contact Designs Mixed-Signal Medium Height 86 μm in-line pad pitch	Short Pads for	135 μm in–line pad pitch	
Medium Height		388 μm pad height	
		86 μm in–line pad pitch	
		567 μm pad height	

^{*}Routed gate density.

MEMORY OPTIONS

SRAM		
Single Port Synchronous*	191 μm ² /bit (64 k bit memory)	
Dual Port Synchronous*	567 μm ² /bit (64 k bit memory)	
ROM		
Asynchronous*	14.65 μm ² /bit (64 k bit memory)	
EEPROM		
NASTEE (No Additional Steps EEPROM)	Vector (1x4 up to 1x32)	
	Array (2x4 up to 32x32)	

^{*}Compiled

CAD TOOL COMPATIBILITY

Digital Design	Synopsys Design Compiler
	Cadence Verilog
Analog Design	Cadence DFII (4.4.6)
	Spectre
Place and Route	Synopsys Apollo, Astro
	Cadence Silicon Ensemble
Physical Verification	Mentor Calibre

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